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AMENDMENTS TO THE CLAIMS:

Please cancel claims 1-20 and 25-30 without prejudice or disclaimer.

Claims 1-20. (Canceled)

Claim 21. (Currently amended) A method for manufacturing a group III nitride compound semiconductor device, comprising:
irradiating a surface of a wafer comprising a group III nitride compound semiconductor with ultraviolet rays to thereby clean a resist residue from said surface of said wafer,
wherein said ultraviolet rays cause a reaction of oxygen molecules to form stimulated oxygen atoms having a strong oxidative power at said surface of said wafer.

Claim 22. (Previously presented) A method for manufacturing a group III nitride compound semiconductor device according to claim 21, wherein said ultraviolet rays have a central wavelength of 172 nm.

Claim 23. (Previously presented) A method for manufacturing a group III nitride compound semiconductor device according to claim 21, wherein said ultraviolet rays are emitted from an excimer lamp.

Claim 24. (Previously presented) A method for manufacturing a group III nitride compound semiconductor device according to claim 21, wherein said irradiating said surface is carried out on a p-type semiconductor layer.

Claims 25 - 30. (Canceled)

Claim 31. (New) A method for manufacturing a group III nitride compound semiconductor device according to claim 21, wherein said stimulated oxygen atoms oxidize an organic contamination on said surface of said wafer into CO, CO₂ and H₂O which flies up

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from said surface of said light-emitting device.

Claim 32. (New) A method for manufacturing a group III nitride compound semiconductor device according to claim 21, further comprising:

forming a resist layer on a group III nitride compound semiconductor layer; and
patterning said resist layer,

wherein said irradiating said surface of said wafer is performed after said patterning said resist layer.

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